

FIG. 2

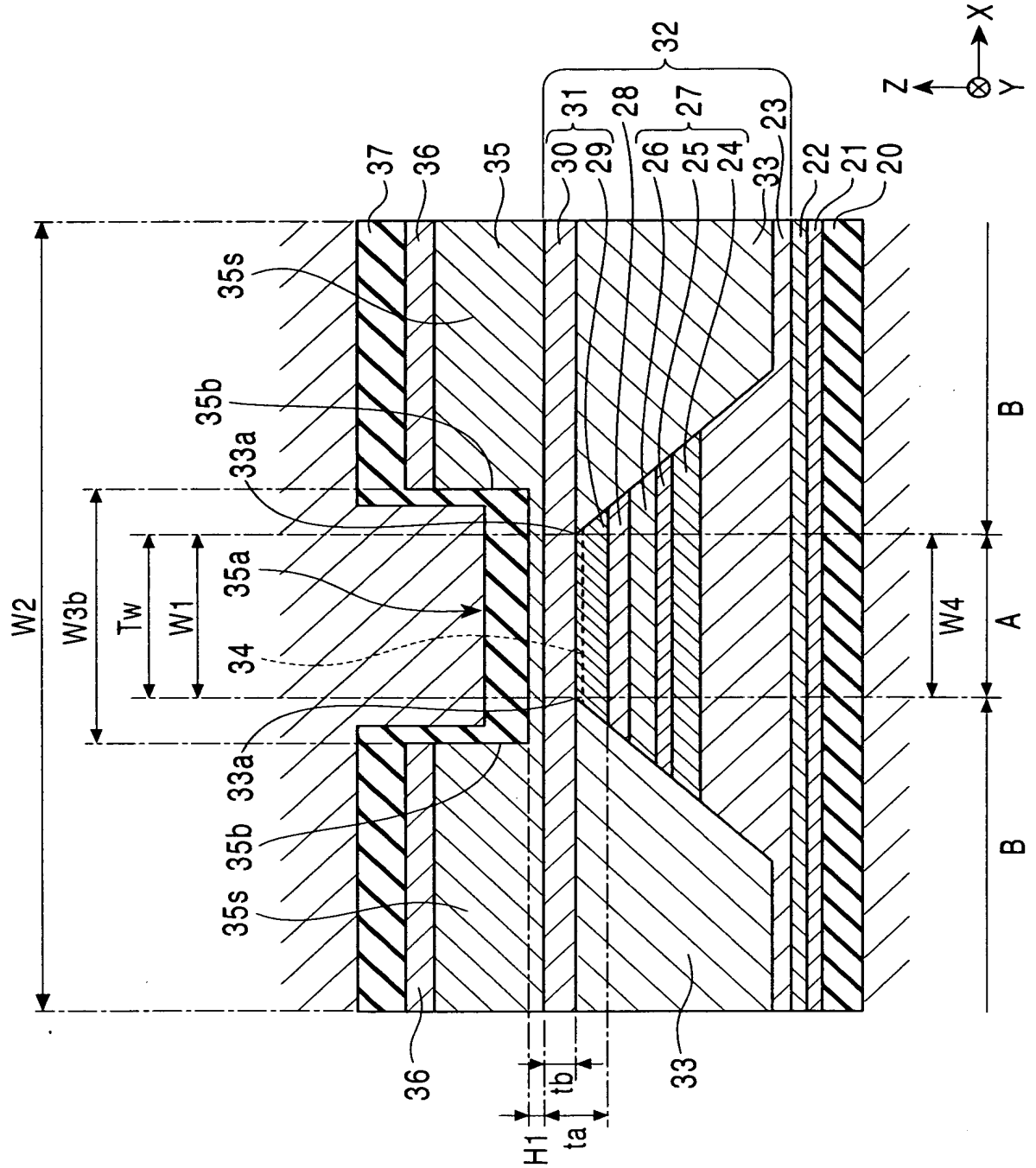


FIG. 3

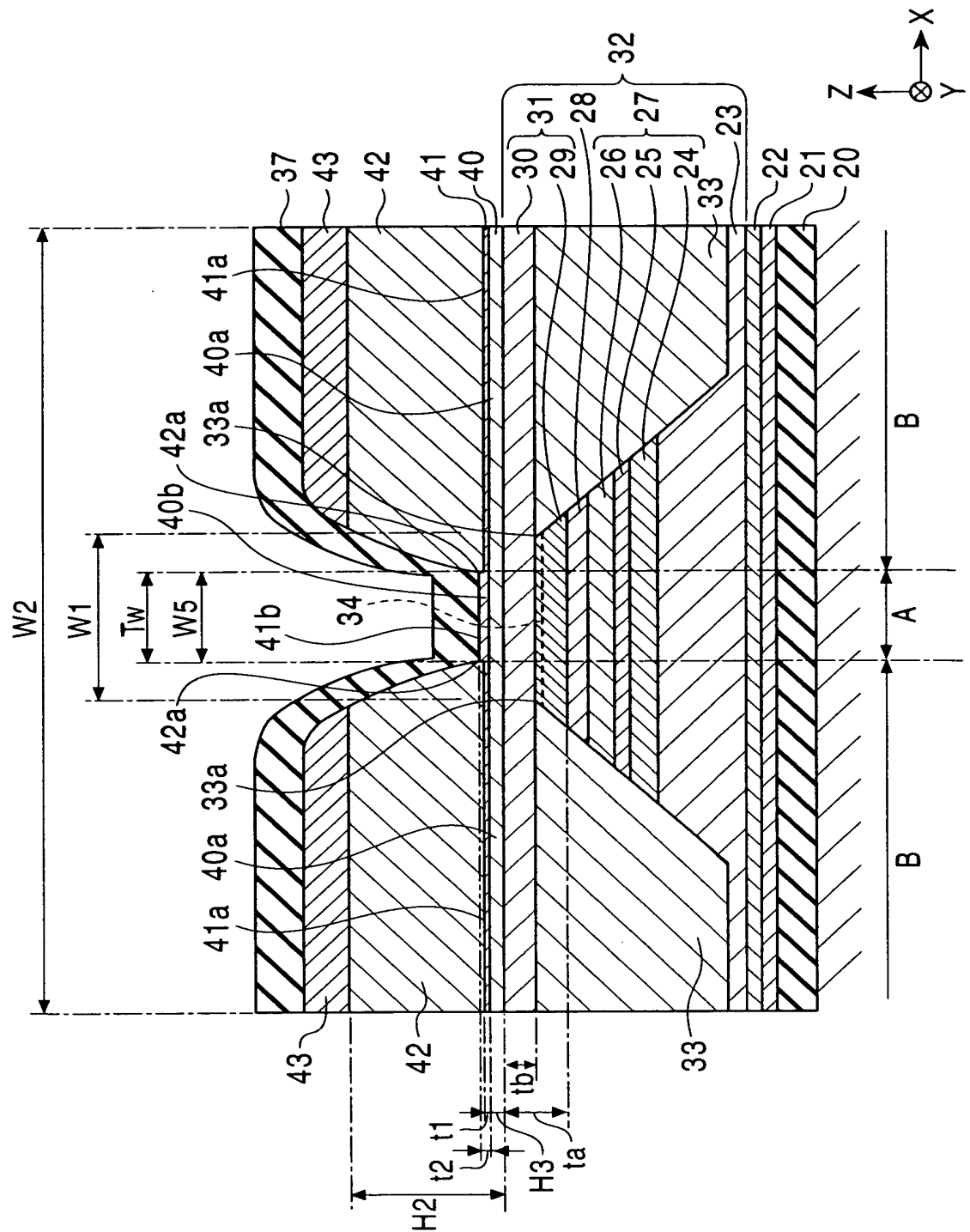


FIG. 4

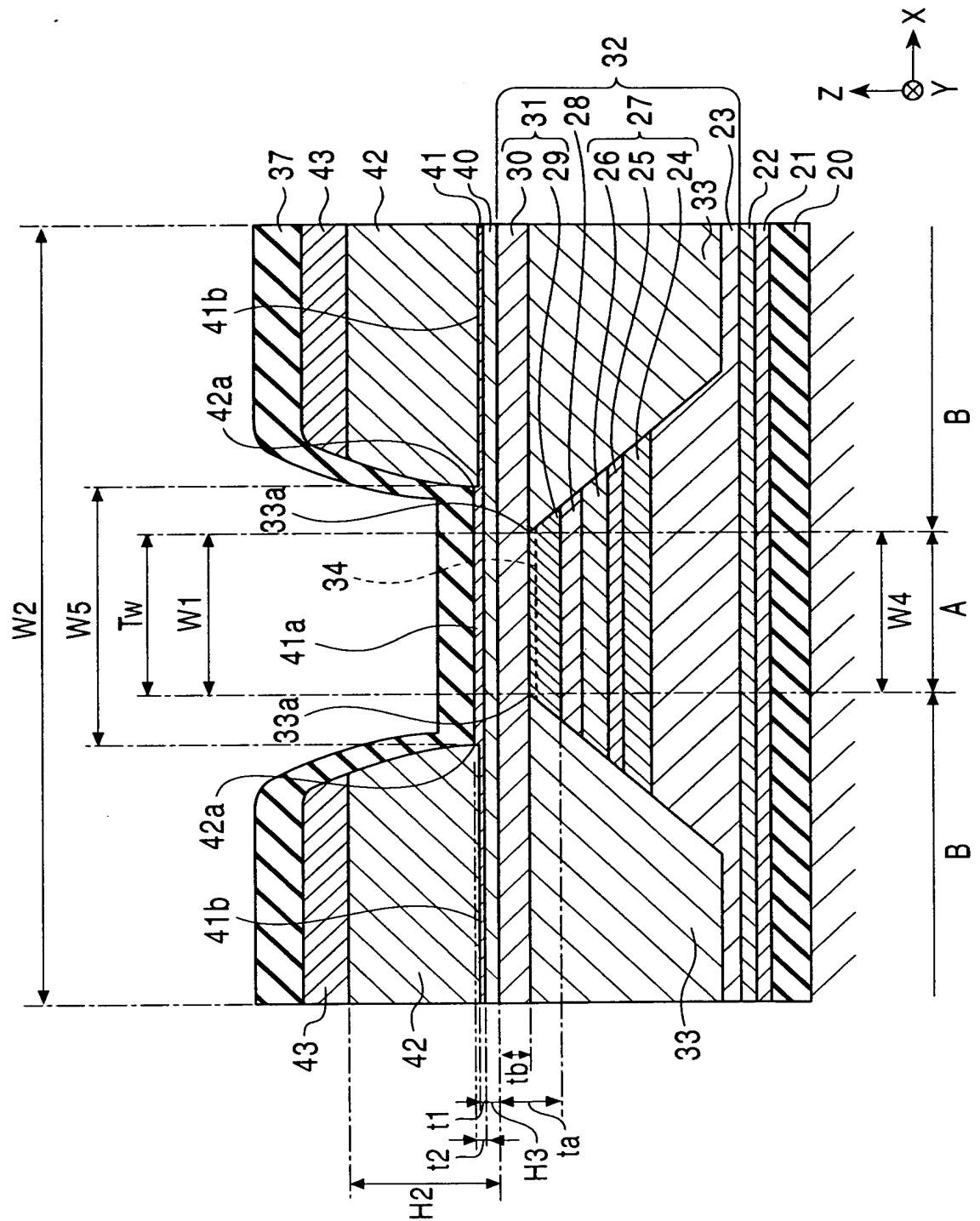


FIG. 5

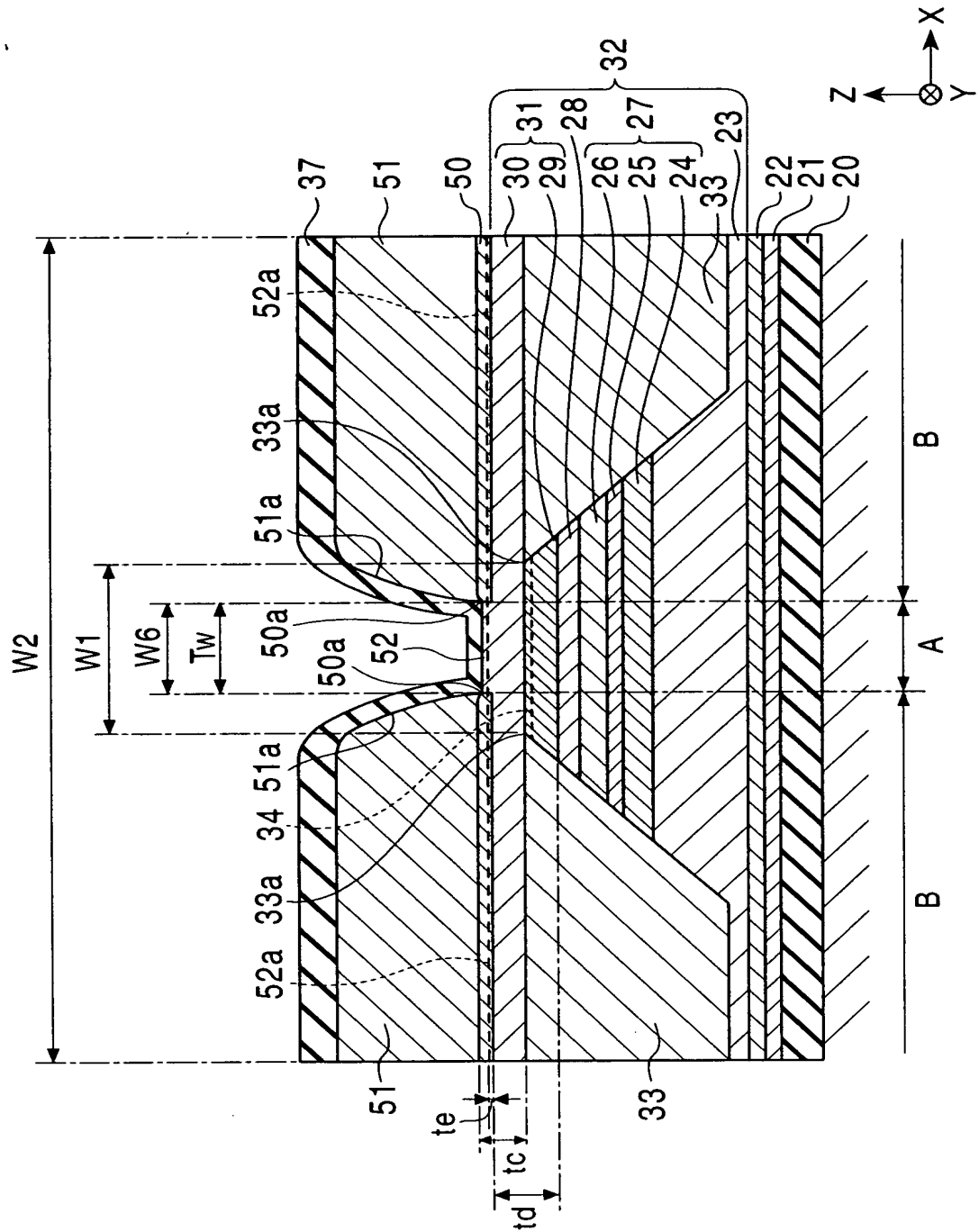


FIG. 6

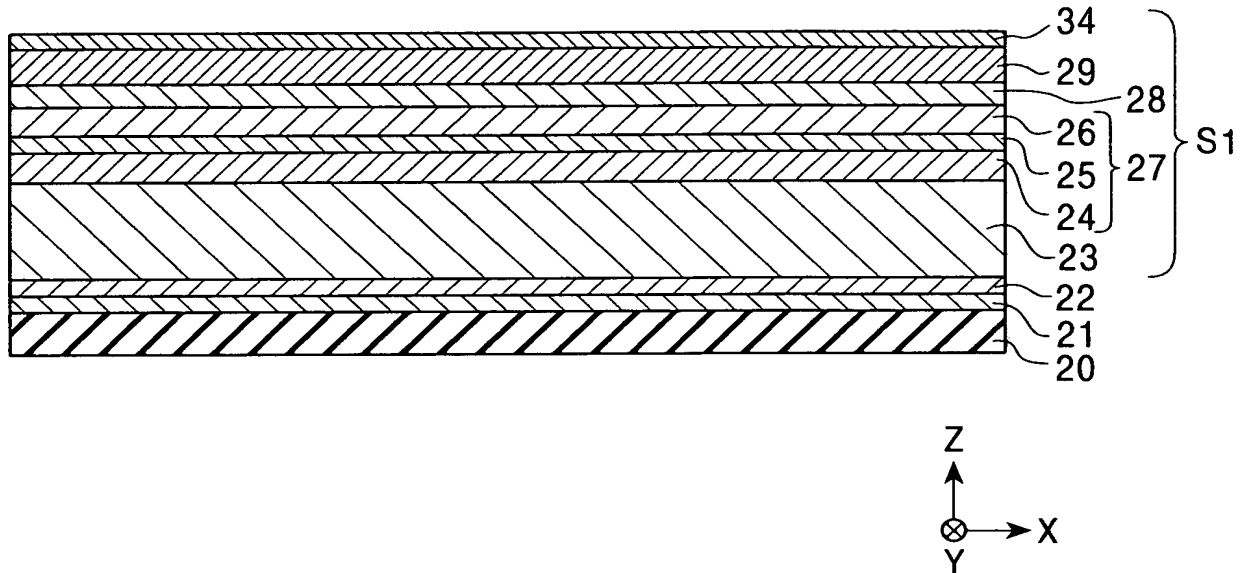
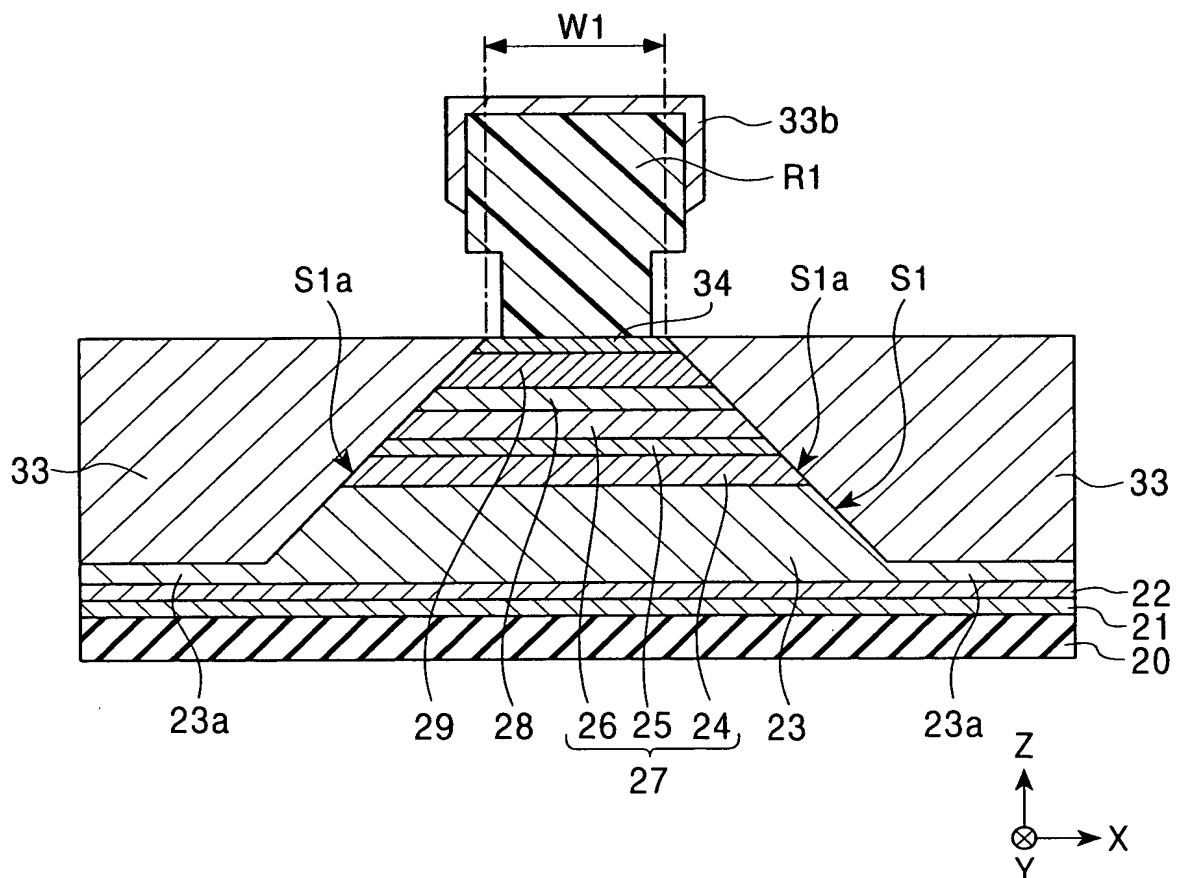


FIG. 7



This diagram shows a cross-sectional view of the semiconductor device in the XZ plane. The device features a substrate 20 with a bottom layer 21 and a top layer 22. A central region 23 contains a stack of layers 24, 25, and 26, which are collectively labeled as 27. This central region is flanked by side regions 23a. Above the central region, a trapezoidal structure 34 is formed, consisting of a top layer 34 and a bottom layer 33. The side regions 23a are also labeled S1a. A coordinate system is shown in the bottom right corner, with the Z-axis pointing upwards and the X-axis pointing to the right. The Y-axis is indicated by a circle with a cross, pointing out of the page.

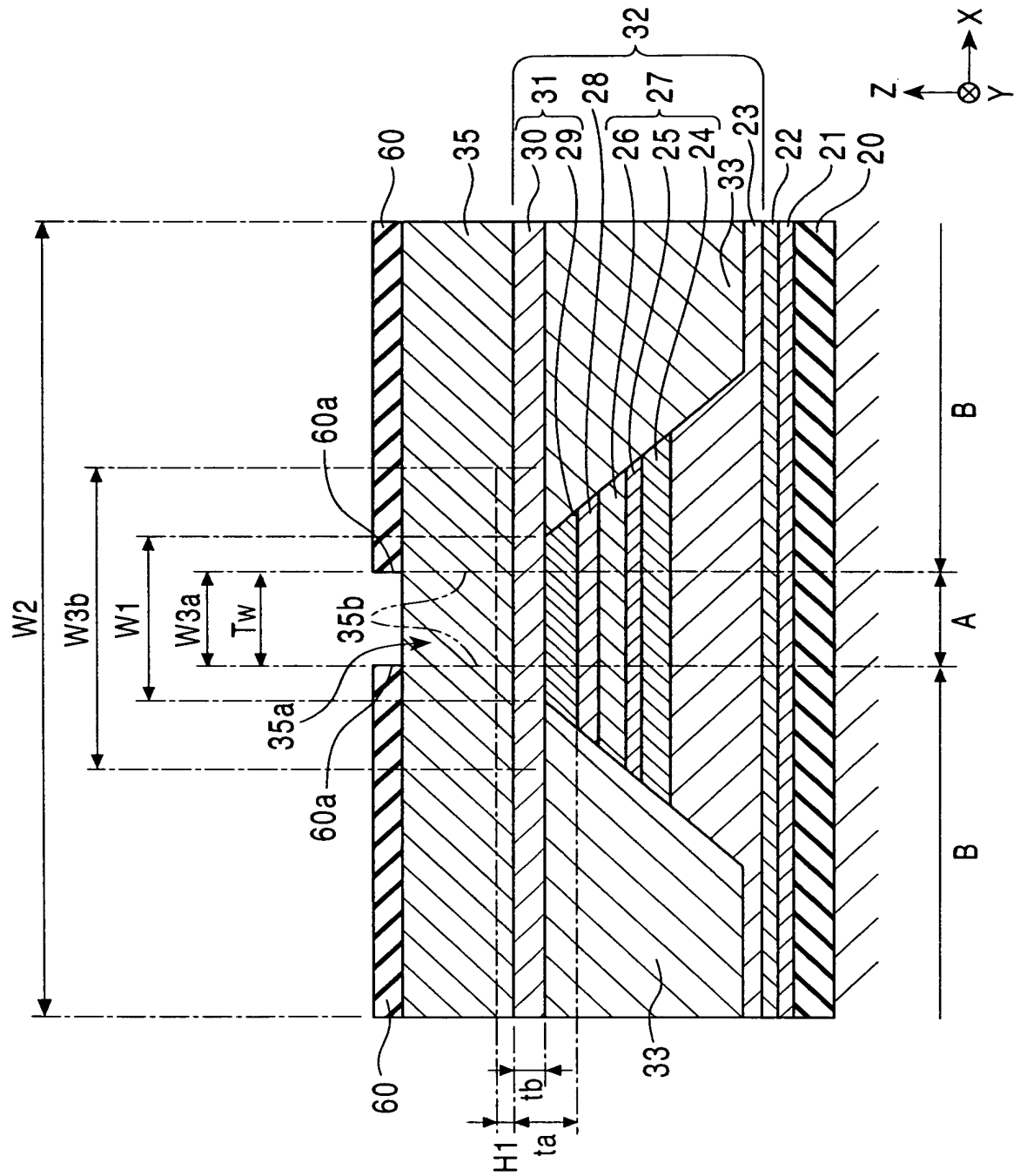
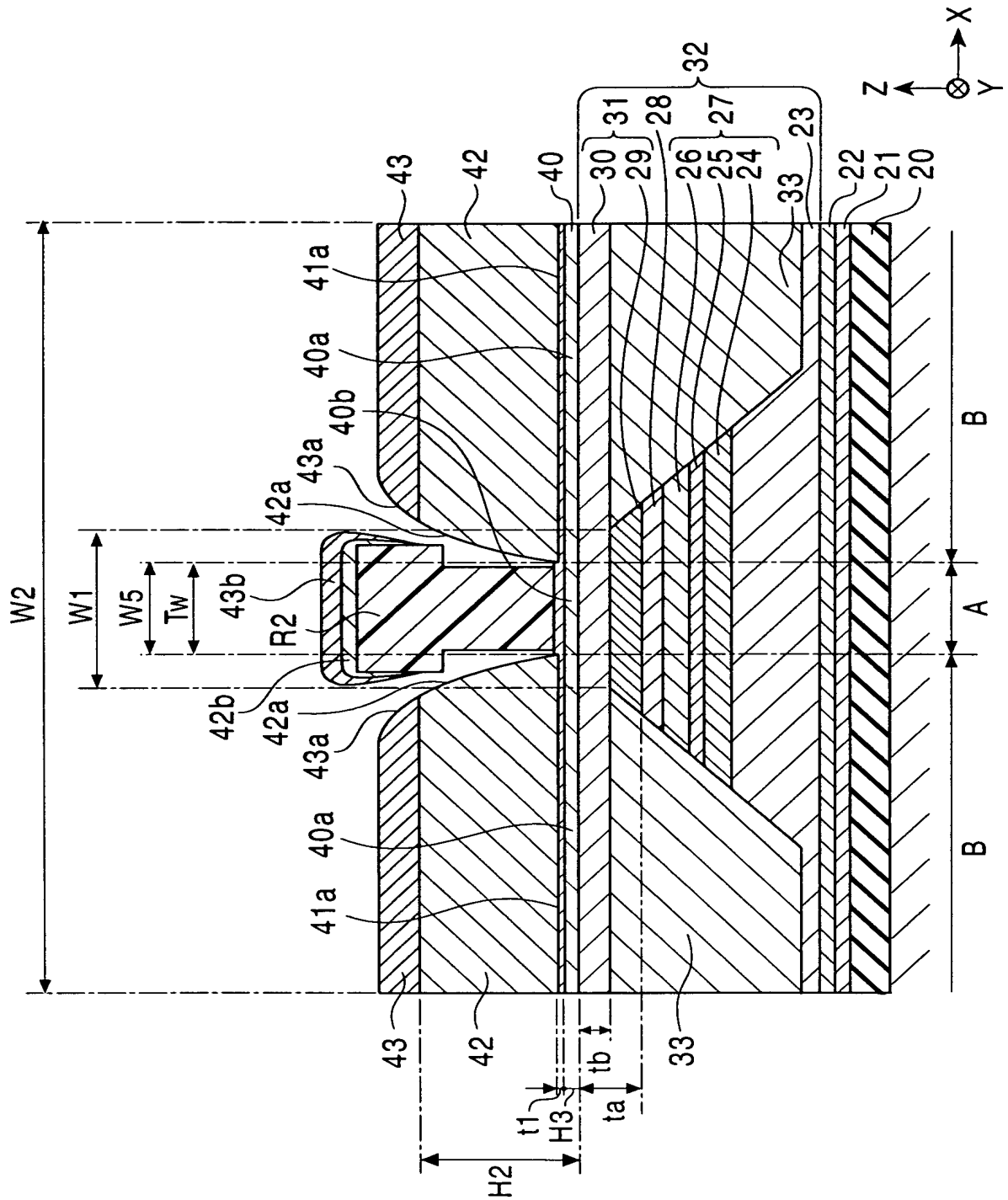
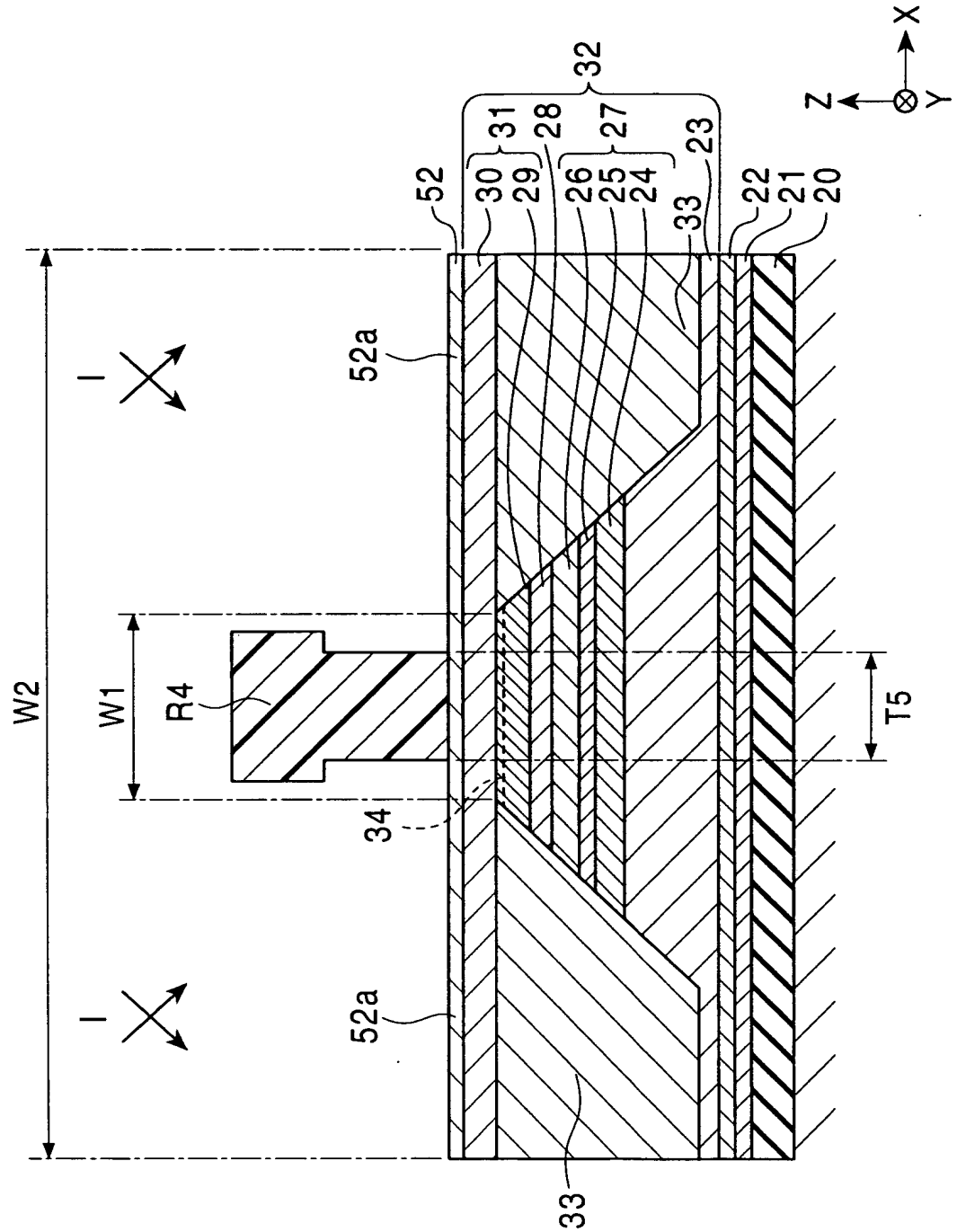


FIG. 11





[illegible]

FIG. 14

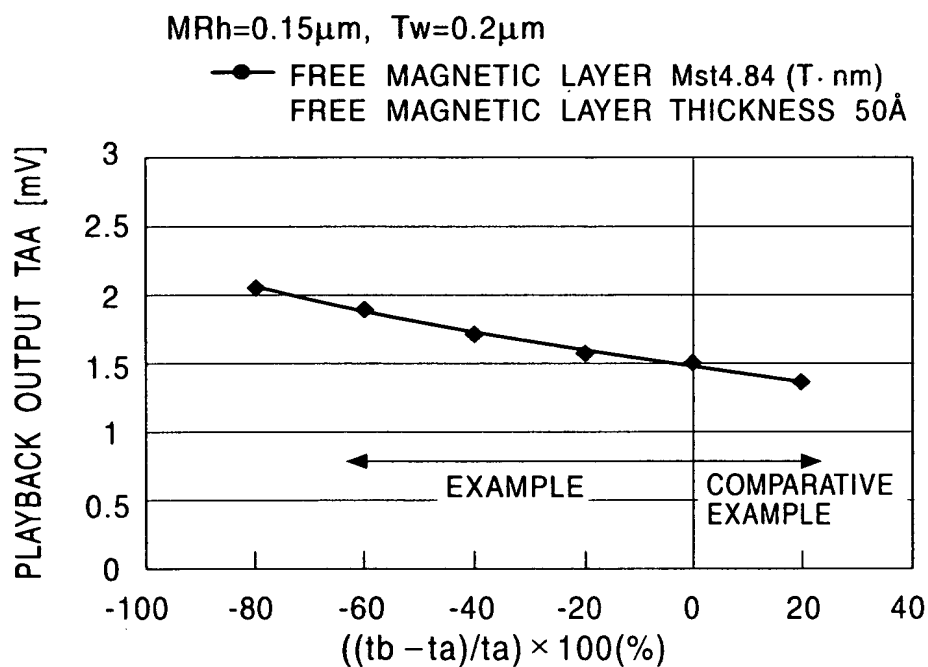


FIG. 15
PRIOR ART

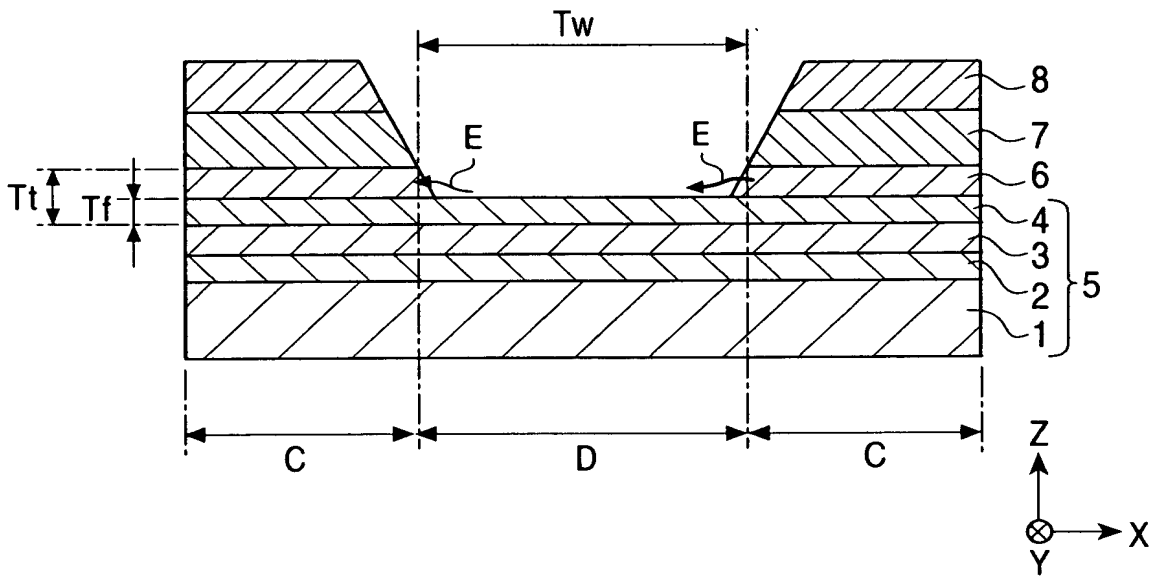


FIG. 16
PRIOR ART

